NSN 5961-01-562-9465

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-562-9465 **Inclosure Material:** Glass **Overall Height:** 1.940 inches **End Application:** C-5m Voltage Rating In Volts Per Characteristic: 64.6 breakdown voltage, instantaneous **Power Rating Per Characteristic:** 1500.00 watts peak pulse output power **Maximum Operating Tempurature Per Measurement Point:** -65.00 degrees celsius ambient air and 175.00 degrees celsius ambient air **Product Name:** Diode, apu circuit **Special Features:** Reverse stand-off volatage: 51.7v, reverse leakage current: 5, breakdown voltage: 64.6v, test current: 20, maximum clamping voltage: 97.1, peak pulse current: 15.4, temperature coefficient: 0.100, maximum reverse leakage current: 400 **Special Test Features:** Peak pulse power: 1500 watts, operating temperature: -65 to 175c, storage temperature: -65 to 175c, steady-state power dissipation @ tl = 75c (3/8"): 5 wattsShelf Life: N/a **Unit Of Measure: Demilitarization:** No

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